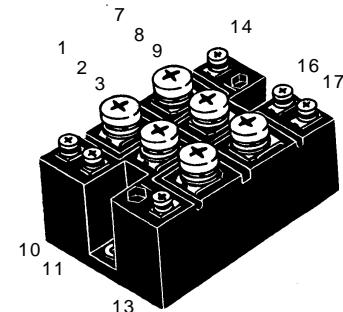
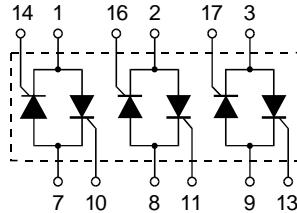


Three Phase AC Controller Modules

$I_{RMS} = 80/95 \text{ A}$
 $V_{RRM} = 800-1400 \text{ V}$

Preliminary data

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type
800	800	VWO 80-08io7
1200	1200	VWO 80-12io7
1400	1400	VWO 80-14io7
		VWO 95-08io7
		VWO 95-12io7
		VWO 95-14io7



Symbol	Test Conditions	Maximum Ratings		Features
		VWO 80	VWO 95	
I_{RMS}	$T_c = 85^\circ\text{C}$, 50 - 400 Hz (per phase)	82	96	A
I_{TRMS}	$T_{VJ} = T_{VJM}$	59	69	A
I_{TAVM}	$T_c = 85^\circ\text{C}$; (180° sine)	37	44	A
I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1000 1100	1150 1230	A
	$T_{VJ} = T_{VJM}$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	900 1000	1000 1100	A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	5000 5080	6600 6280	A^2s
	$T_{VJ} = T_{VJM}$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	4050 4200	5000 5080	A^2s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$ repetitive, $I_T = 150 \text{ A}$ $f = 50 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$ non repetitive, $I_T = I_{TAVM}$ $di_G/dt = 0.3 \text{ A}/\mu\text{s}$	100	500	$\text{A}/\mu\text{s}$
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	1000	1000	$\text{V}/\mu\text{s}$
P_{GM}	$T_{VJ} = T_{VJM}$ $t_p = 30 \mu\text{s}$ $I_T = I_{TAVM}$ $t_p = 300 \mu\text{s}$	10	5	W
P_{GAVM}		0.5	0.5	W
V_{RGM}		10	10	V
T_{VJ}		-40...+125	-40...+125	$^\circ\text{C}$
T_{VJM}		125	125	$^\circ\text{C}$
T_{stg}		-40...+125	-40...+125	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$ $I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	2500	3000	$\text{V}\sim$
M_d	Mounting torque (M5) Terminal connection torque (M3; M5)	5/44±15 % 1.5/13±15 %	Nm/lb.in. Nm/lb.in.	
Weight	typ.	180	180	g

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated.
 IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Test Conditions	Characteristic Values	
		VWO 80	VWO 95
I_D, I_R	$T_{VJ} = T_{VJM}; V_R = V_{RRM}; V_D = V_{DRM}$	≤ 5	5 mA
V_T	$I_T = 150 \text{ A}; T_{VJ} = 25^\circ\text{C}$	≤ 1.65	1.57 V
V_{TO}	For power-loss calculations only	0.85	0.85 V
r_T		5.2	4.8 mΩ
V_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	≤ 1.0	1.0 V
	$T_{VJ} = -40^\circ\text{C}$	≤ 1.6	1.6 V
I_{GT}	$V_D = 6 \text{ V}; T_{VJ} = 25^\circ\text{C}$	≤ 100	100 mA
	$T_{VJ} = -40^\circ\text{C}$	≤ 150	150 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_D = 2/3 V_{DRM}$	≤ 0.2	0.2 V
I_{GD}		≤ 5	5 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$	≤ 200	200 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	≤ 150	150 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = 1/2 V_{DRM}$ $I_G = 0.3 \text{ A}; di_G/dt = 0.3 \text{ A}/\mu\text{s}$	≤ 2	2 μs
t_q	$T_{VJ} = T_{VJM}; I_T = 20 \text{ A}, t_p = 200 \mu\text{s};$ $di/dt = -10 \text{ A}/\mu\text{s}$ $V_R = 100 \text{ V}; dv/dt = 15 \text{ V}/\mu\text{s}; V_D = 2/3 V_{DRM}$	typ. 150	150 μs
R_{thJC}	per thyristor; sine 180°el	0.81	0.66 K/W
	per module	0.135	0.11 K/W
R_{thJK}	per thyristor; sine 180°el	1.0	0.93 K/W
	per module	0.167	0.155 K/W
d_s	Creeping distance on surface	8.0	mm
d_A	Creepage distance in air	4.5	mm
a	Max. allowable acceleration	50	m/s ²

Dimensions in mm (1 mm = 0.0394")

